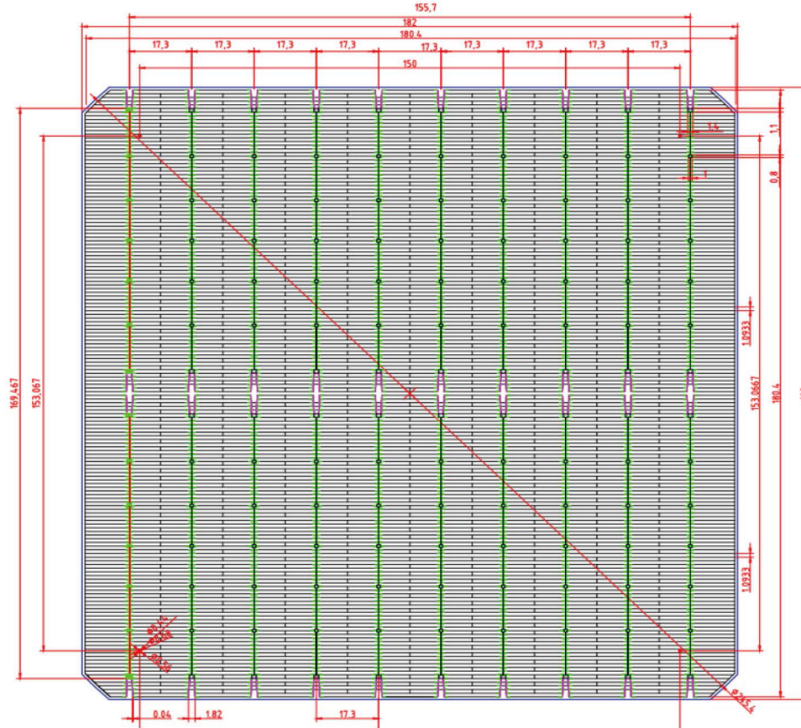


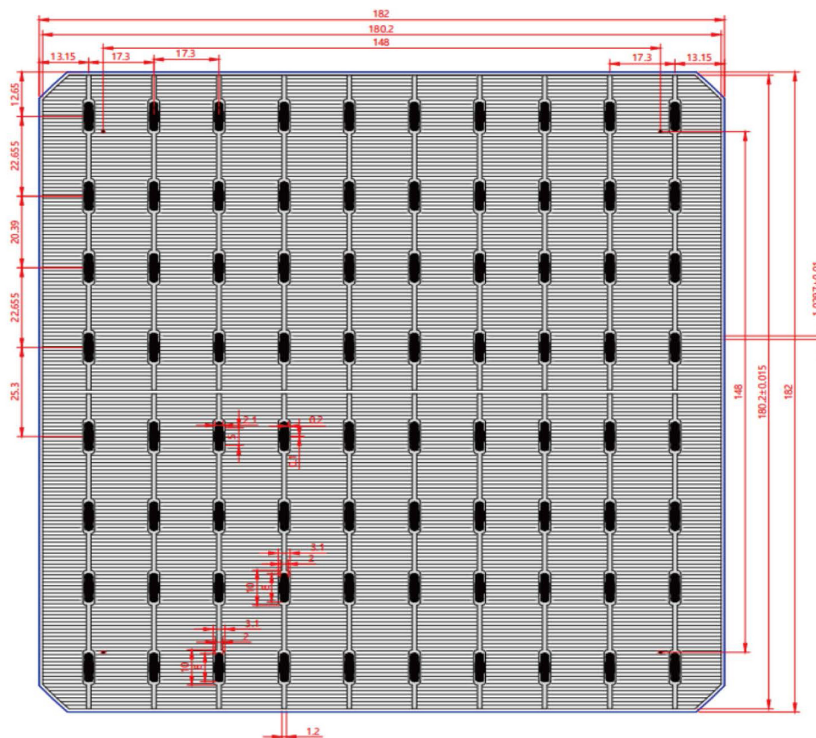


Technical Specification

• 技术图形 Technical drawing



Front



Back

• 电气特性 Electrical Characteristics

Grade	Eff(%)	Pmpp(W)	Vmpp(V)	Ippp(A)	Voc(V)	Isc(A)	FF(%)
1	23.30	7.69	0.591	13.02	0.694	13.649	81.18
2	23.20	7.66	0.589	12.99	0.693	13.627	81.07
3	23.10	7.63	0.588	12.97	0.692	13.619	80.94
4	23.00	7.59	0.586	12.96	0.691	13.612	80.78
5	22.90	7.56	0.584	12.94	0.689	13.607	80.68
6	22.80	7.53	0.583	12.91	0.688	13.579	80.53
7	22.70	7.49	0.581	12.90	0.687	13.577	80.36
8	22.60	7.46	0.580	12.87	0.687	13.534	80.27
9	22.50	7.43	0.579	12.83	0.686	13.510	80.24
10	22.40	7.40	0.578	12.83	0.685	13.500	80.21
11	22.30	7.36	0.576	12.76	0.684	13.489	80.03
12	22.20	7.33	0.575	12.74	0.683	13.486	79.82
13	22.10	7.30	0.574	12.70	0.682	13.426	79.70
14	22.00	7.26	0.572	12.70	0.682	13.402	79.46

标准测试条件下(Under standard test condition) :1000W/m², AM1.5, 25°C

温度系数 Temperature coefficients

开路电压温度系数 Temperature coefficients of open circuit voltage: -0.36%/K

短路电流温度系数 Temperature coefficients of short circuit current: +0.07%/K

最大功率温度系数 Temperature coefficients of maximum power: -0.38%/K

• 机械特征 Mechanical characteristics

尺寸规格 **Dimension:** 182mmx182mm±0.25mm, Φ247mm±0.25mm; 电池厚度 **Cell Thickness:** 160-10/+20μm

正面(一) **Front side:** 二氧化硅+深蓝色氮化硅复合减反膜(PID Free); 主栅宽度: 1.0±0.05mm; 主栅头部呈双叉, 166根副栅线, 正电极为半片设计。

Silicon oxide+blue silicon nitride compound anti-reflection coating(PID Free);The width of the busbar is 1.0±0.05mm;the head of the busbar is forked;the number of the finger is 166;The front side of solar cell is designed as a half sheet.

背面(+) **Back side:** 钝化发射极(氧化铝及氮化硅复合层); 背电极宽度为 2.1±0.1mm, 10根主栅线(铝), 176根副栅线(铝)
Passivated Emitter (AlO_x and SiN_x dual layer) rear contact;The width and length of the Ag electrode is 2.1±0.1mm, the number of the aluminum busbar is 10; the number of the aluminum finger is 176;

可焊性(**Solderability**): 最小剥离强度(Peel strength) ≥1.0N/mm

结果可能会因焊条、焊接方法及条件而不同。Results may vary depending on the conditions.